

CLAIMS

1. A semiconductor device, wherein said semiconductor device is formed, after a plurality of identical semiconductor chips that are formed on a semiconductor wafer, by dividing the semiconductor chips in a unit of one or a plurality according to a result of a quality test for each semiconductor chips.

2. The semiconductor device according to claim 1, wherein said semiconductor chips are memory chips.

3. A semiconductor device, wherein said semiconductor device is formed, after wiring, resin sealing, and terminal formation are carried out for a plurality of identical semiconductor chips, by dividing the semiconductor chips in a unit of one or a plurality according to a result of a quality test or each semiconductor chips.

4. The semiconductor device according to claim 3, wherein said semiconductor chips are memory chips.

5. A method for manufacturing the semiconductor device, comprising:

a first step of forming a plurality of identical semiconductor chips on a semiconductor wafer;

a second step of carrying out a quality test for each of a plurality of said semiconductor chips formed on said semiconductor wafer; and

a third step of dividing one or a plurality pieces of said semiconductor chips on the basis of a result of said quality test.

6. The method for manufacturing the semiconductor device according to claim 5, wherein said semiconductor chips are memory chips.

7. The method for manufacturing the semiconductor device according to claim 5, wherein said plurality of semiconductor chips are divided in every group made of four pieces if four pieces are possible to handle, every two pieces if four pieces are impossible but two are possible to handle, and every one piece if two are impossible to handle, after said quality test is carried out.

8. A method for manufacturing the semiconductor device, comprising:

a first step of forming a plurality of identical semiconductor chips on a semiconductor wafer;

a second step of carrying out wiring, resin sealing, terminal formation for a plurality of said semiconductor chips formed on said semiconductor wafer;

a third step of carrying out a quality test of each of a plurality of said semiconductor chips, which is formed on said semiconductor wafer, by using said terminal formed by said second step; and

a fourth step of dividing one or a plurality of said semiconductor chips on the basis of a result of said quality test.

9. The method for manufacturing the semiconductor device according to claim 8, wherein said semiconductor chips are memory chips.

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10. The method for manufacturing the semiconductor device according to claim 8, wherein said plurality of semiconductor chips are divided in every group made of four pieces if four pieces are possible to handle, every two pieces if four pieces are impossible but two are possible to handle, and every one piece if two are impossible to handle, after said quality test is carried out.

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